Supplementary Information for “Triazolylidene Small Molecule Inhibitor for Area-Selective Atomic Layer Deposition of High *k*-Dielectric Materials”

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Figure 1: Cycles of dielectric overlayers on Tz protected surfaces compared with SMI free surfaces (*left*); SEM images of patterned substrates after overlayed deposition (*right*).

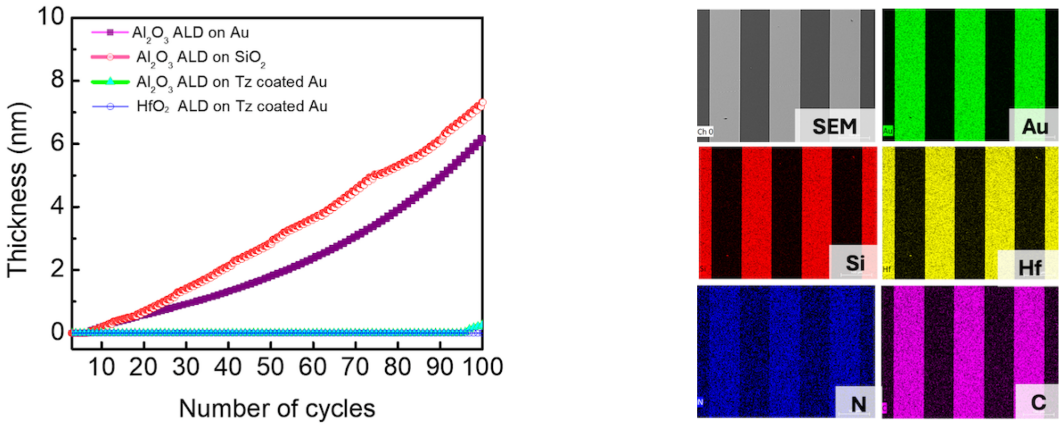

Figure 2: Proof of principle for the functionality of Tz SMIs for bottom up manufacturing of a basic field effect transistor (FET). FET architecture and conductivity data (*right*); SEM-EDX after bottom up fabrication (left).